



YJS03NP10A

NMOS Electrical Characteristics ($T_j=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250$	100	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=100V, V_{GS}=0V$	-	-	1	
		$V_{DS}=100V, V_{GS}=0V, T_j=150$	-	-	100	



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Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250$	-100	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-100V, V_{GS}=0V$	-	-	-1	
		$V_{DS}=-100V, V_{GS}=0V, T_J=150$	-	-	-100	
Gate-Body Leakage Current	I_{GSS}	$V_{GS}= \pm 20V, V_{DS}=0V$	-	-	± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250$	-1	-1.7	-2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-3A$ V_{GS}	-	85	110	m



NMOS Typical Electrical and Thermal Characteristics Diagrams

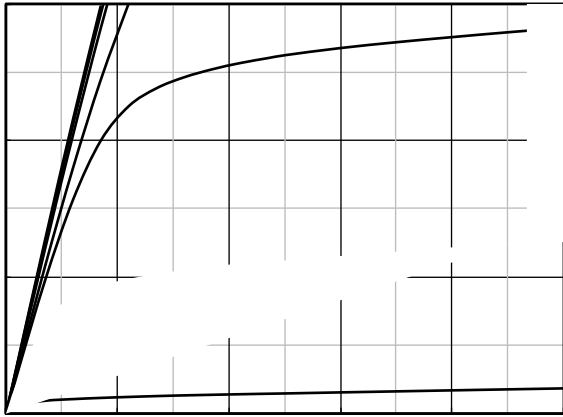


Figure 1. Output Characteristics

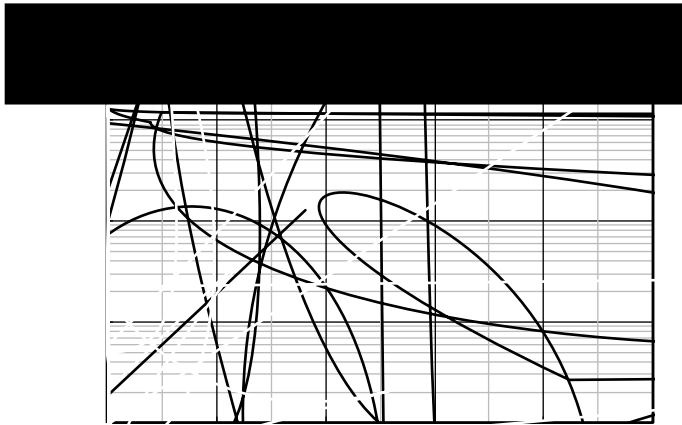
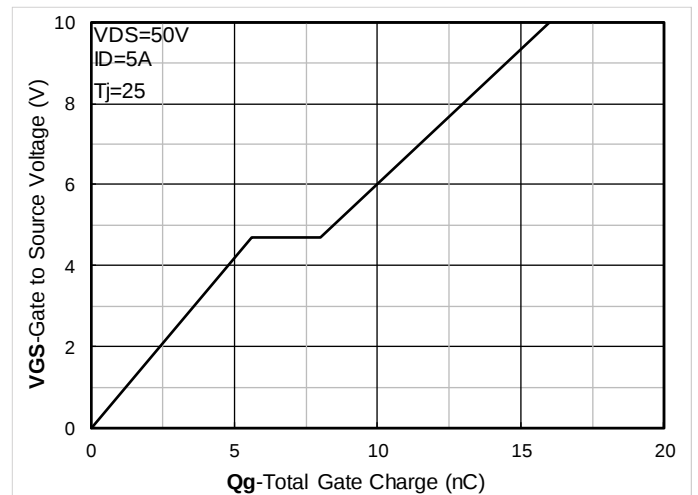


Figure 2. Transfer Characteristics





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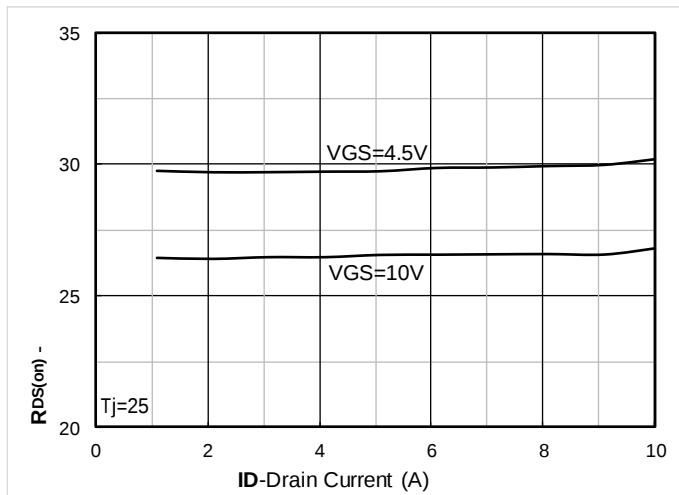


Figure 7. $R_{DS(on)}$ VS Drain Current

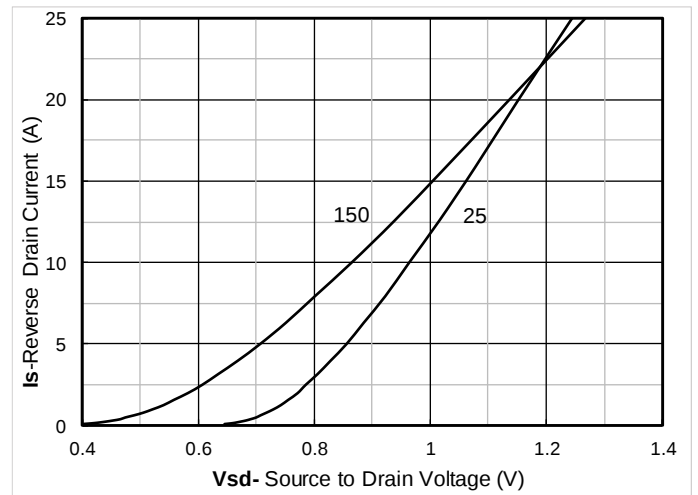


Figure 8. Forward characteristics of reverse diode

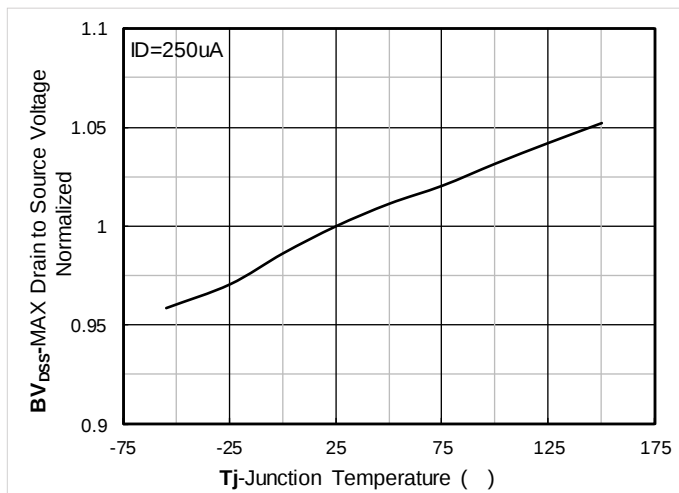


Figure 9. Normalized breakdown voltage

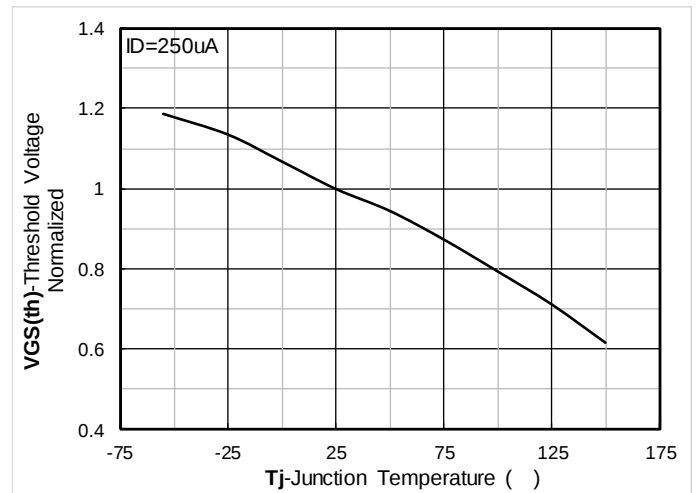


Figure 10. Normalized Threshold voltage

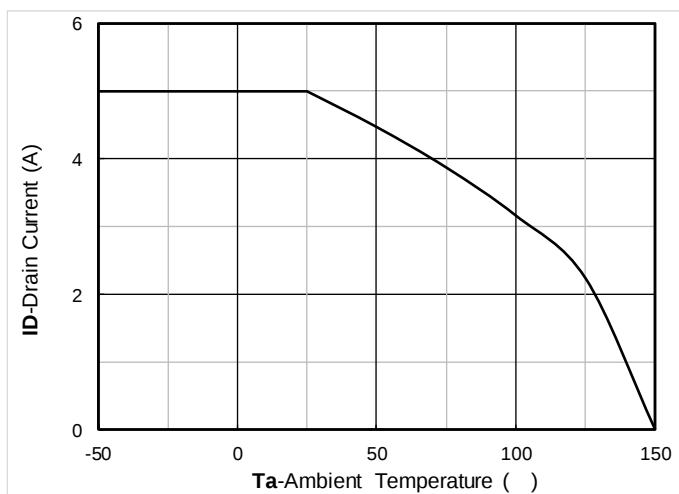


Figure 11. Current dissipation

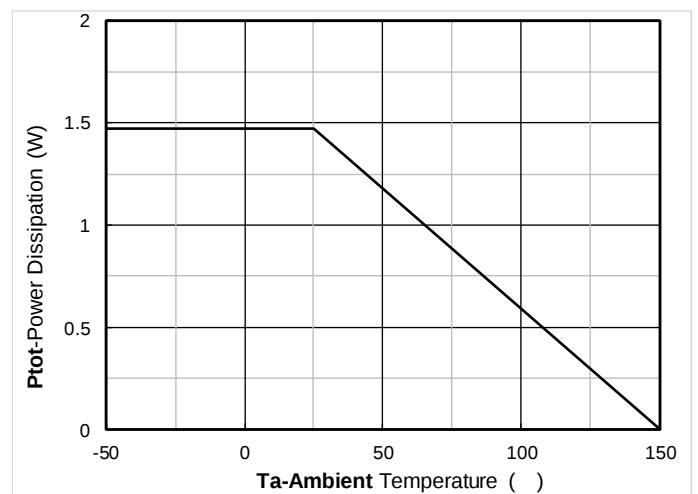


Figure 12. Power dissipation

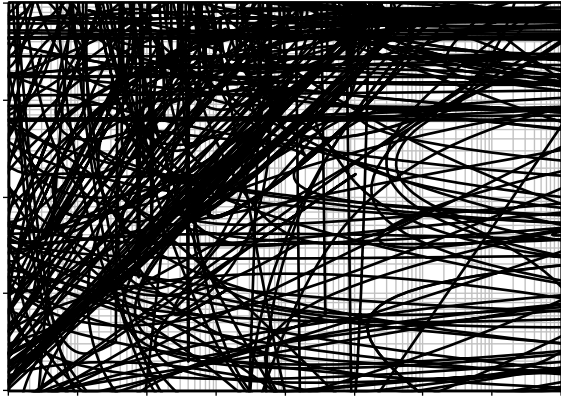


Figure 13. Maximum Transient Thermal Impedance

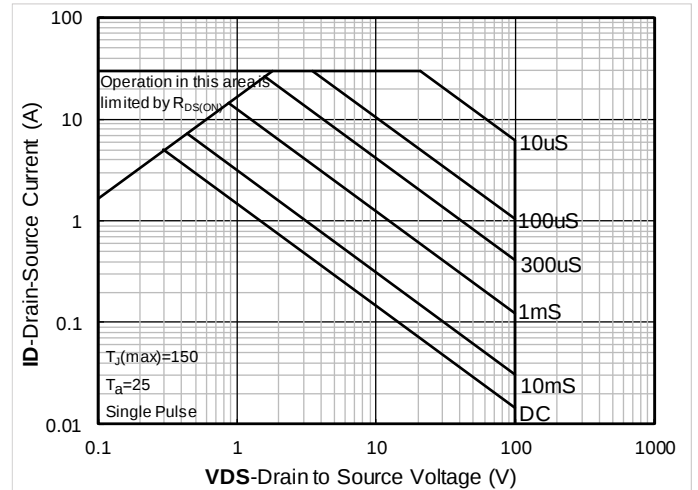


Figure 14. Safe Operation Area

PMOS Typical Electrical and Thermal Characteristics Diagrams

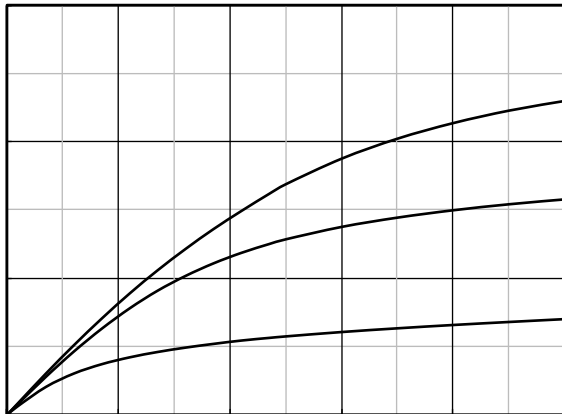


Figure 1. Output Characteristics

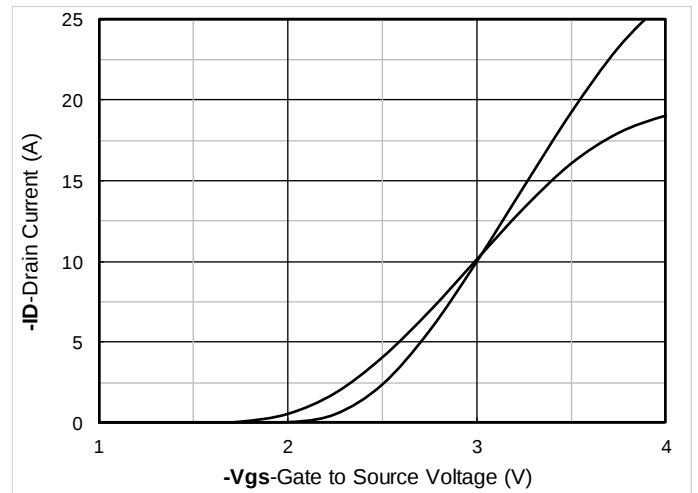


Figure 2. Transfer Characteristics

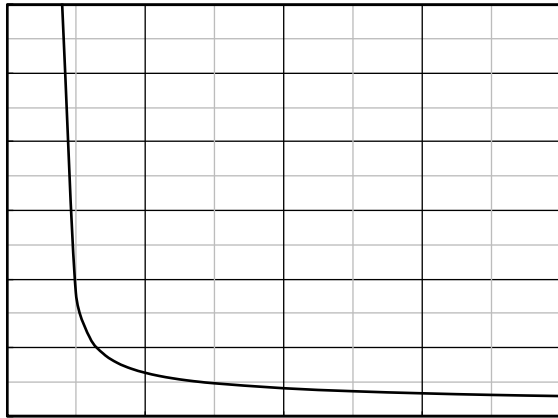


Figure 5. On-Resistance vs Gate to Source Voltage

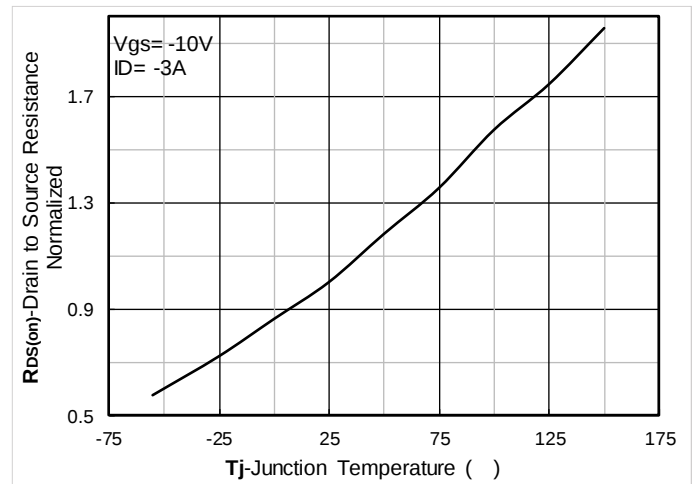


Figure 6. Normalized On-Resistance

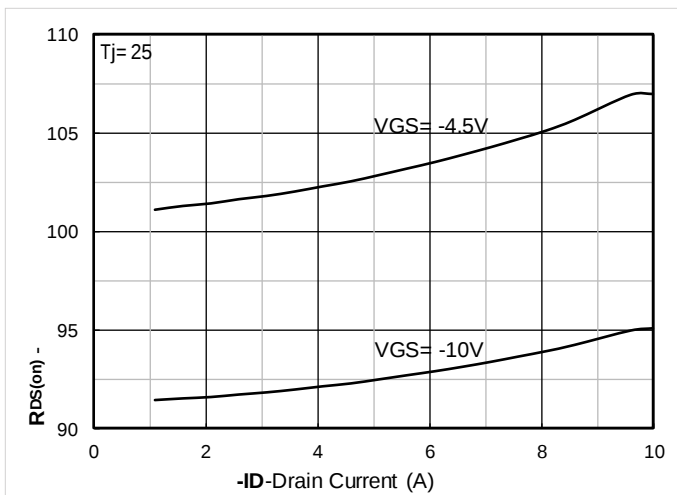


Figure 7. $R_{DS(on)}$ VS Drain Current

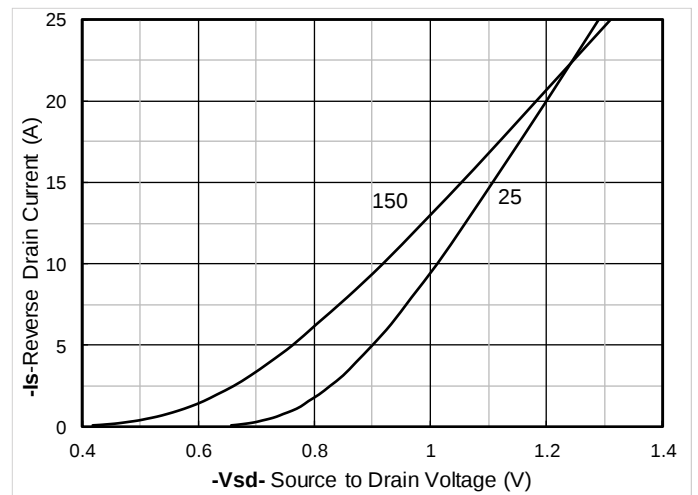


Figure 8. Forward characteristics of reverse diode

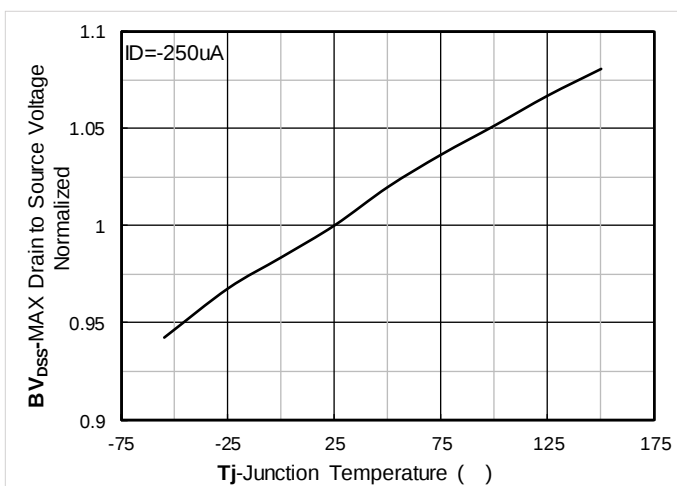


Figure 9. Normalized breakdown voltage

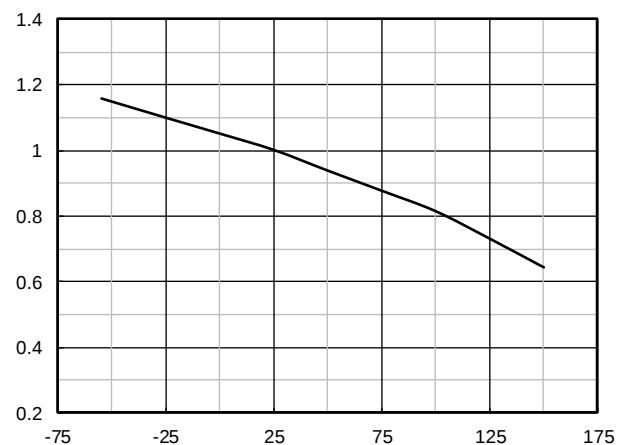
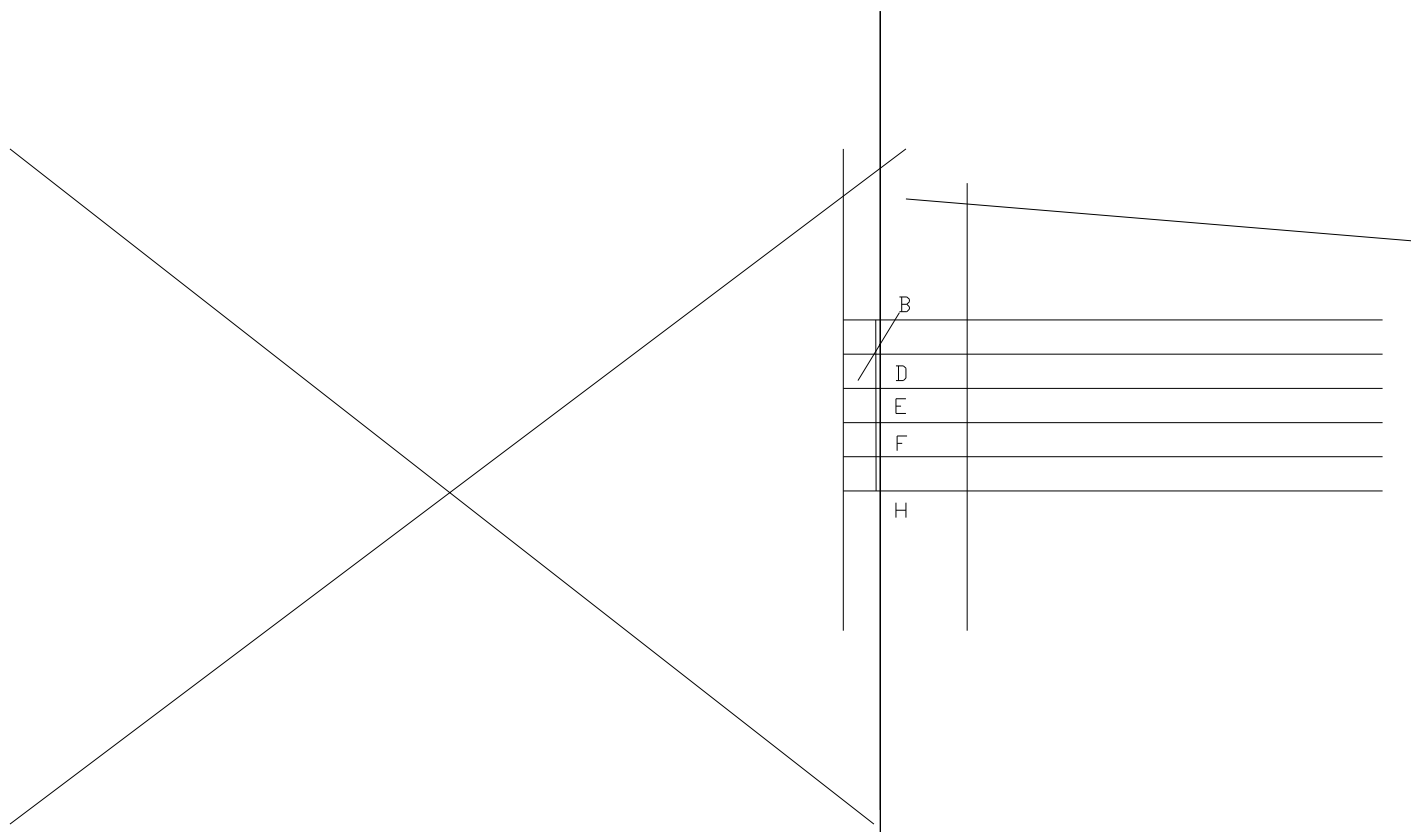


Figure 10. Normalized Threshold voltage



SOP-8 Package information





YJS03NP10A

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